

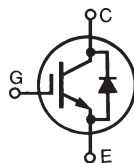
# High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

## IXBF32N300

$$V_{CES} = 3000V$$

$$I_{C90} = 22A$$

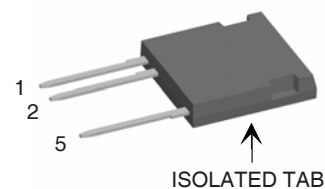
$$V_{CE(sat)} \leq 3.2V$$



(Electrically Isolated Tab)

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_C = 25^\circ C$ to $150^\circ C$	3000	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	3000	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	40	A
$I_{C90}$	$T_C = 90^\circ C$	22	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	250	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 80$ $V_{CES} \leq 2400$	A V
$P_C$	$T_C = 25^\circ C$	160	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$ $T_{SOLD}$	1.6mm (0.062 in.) from Case for 10s Plastic Body for 10 seconds	300 260	$^\circ C$ $^\circ C$
$F_C$	Mounting Force	20..120 / 4.5..27	Nm/lb.in.
$V_{ISOL}$	50/60Hz, 1 Minute	3000	V
<b>Weight</b>		5	g

### ISOPLUS i4-Pak™



1 = Gate      5 = Collector  
2 = Emitter

### Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 3000V Electrical Isolation
- High Blocking Voltage
- International Standard Package
- Low Conduction Losses

### Advantages

- Low Gate Drive Requirement
- High Power Density

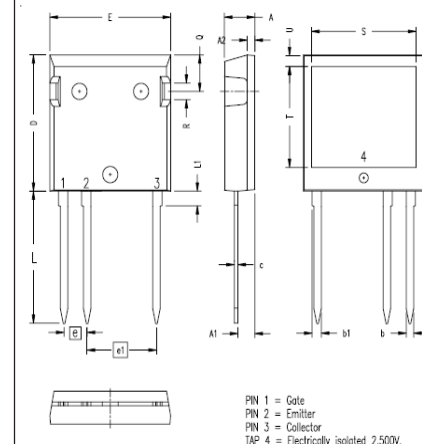
### Applications:

- Switched-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	2.5		5.0 V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 2 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 32A$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ C$		2.8 3.5	3.2 V V

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 32\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	16	26	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3140	pF
$C_{oes}$			124	pF
$C_{res}$			40	pF
$Q_g$	$I_C = 32\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$		142	nC
$Q_{ge}$			20	nC
$Q_{gc}$			57	nC
$t_{d(on)}$	<b>Resistive Switching Times, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 32\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}, R_G = 2\Omega$		50	ns
$t_r$			185	ns
$t_{d(off)}$			160	ns
$t_f$			720	ns
$t_{d(on)}$		<b>Resistive Switching Times, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 32\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}, R_G = 2\Omega$		58
$t_r$			515	ns
$t_{d(off)}$			165	ns
$t_f$			630	ns
$R_{thJC}$				0.78
$R_{thCS}$		0.15		$^\circ\text{C/W}$

### ISOPLUS i4-Pak™ (HV) (IXBF) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.085	1.17	2.16
b	.045	.055	1.14	1.40
b1	.058	.068	1.47	1.73
C	.020	.029	0.51	0.74
D	.819	.840	20.80	21.34
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
e1	.450 BSC		11.43 BSC	
L	.780	.840	19.81	21.34
L1	.083	.102	2.11	2.59
Q	.210	.244	5.33	6.20
R	.100	.180	2.54	4.57
S	.660	.690	16.76	17.53
T	.590	.620	14.99	15.75
U	.065	.080	1.65	2.03

### Reverse Diode

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 32\text{A}, V_{GE} = 0\text{V}$			2.1 V
$t_{rr}$	$I_F = 16\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		1.5	$\mu\text{s}$
$I_{RM}$		$V_R = 100\text{V}, V_{GE} = 0\text{V}$		33

Note 1: Pulse Test,  $t \leq 300\mu\text{s}$ , Duty Cycle,  $d \leq 2\%$ .

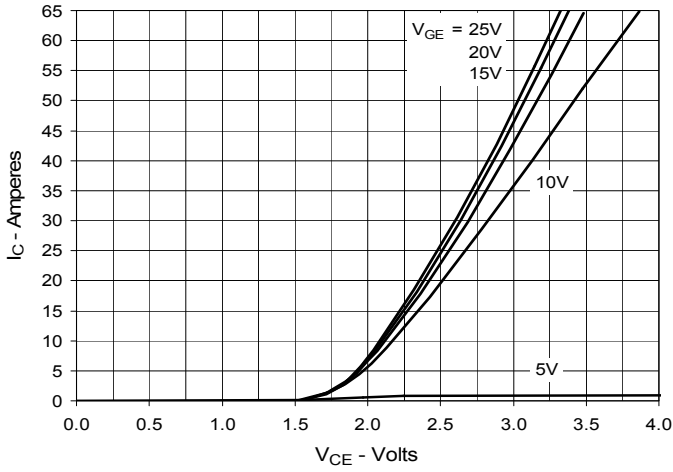
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

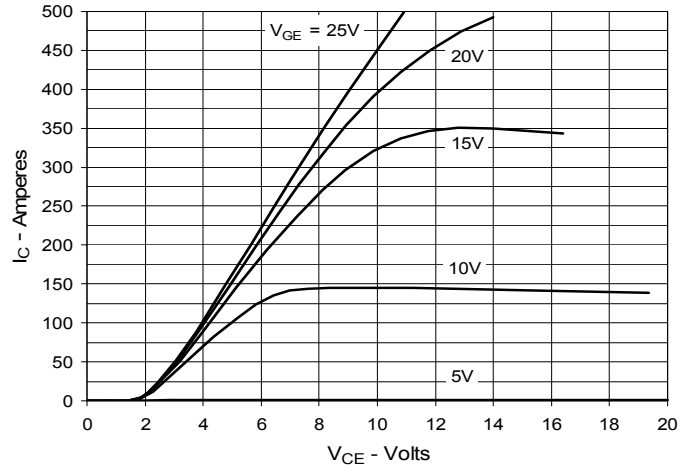
IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

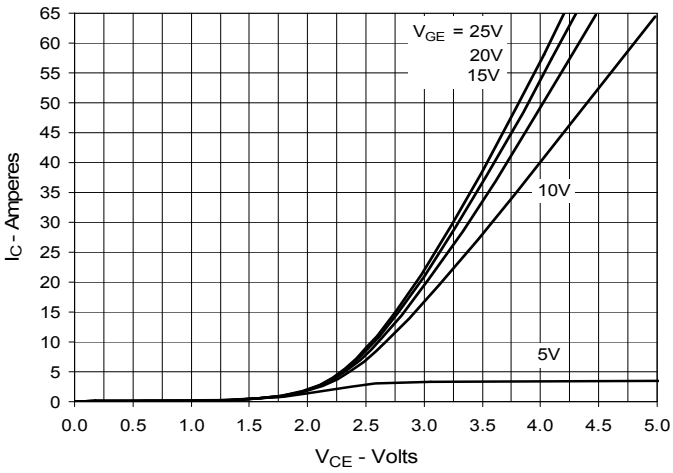
**Fig. 1. Output Characteristics @ 25°C**



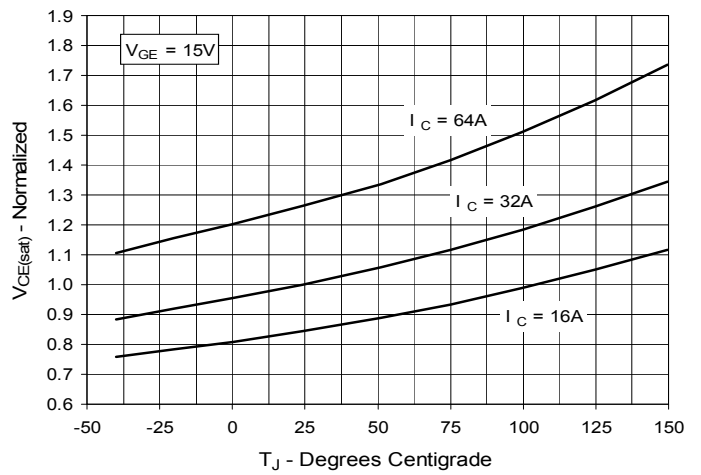
**Fig. 2. Extended Output Characteristics @ 25°C**



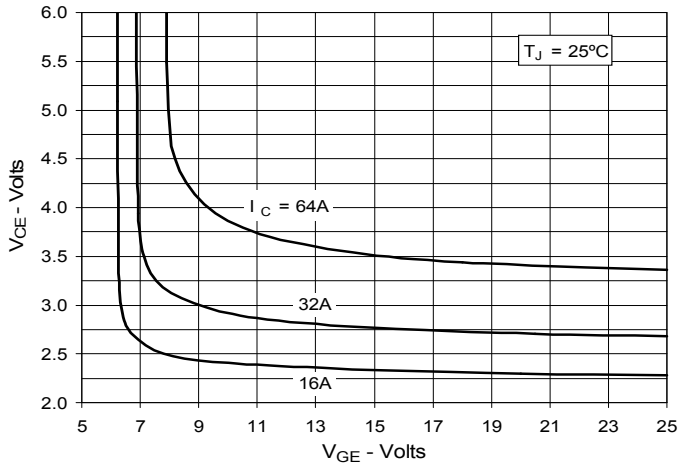
**Fig. 3. Output Characteristics @ 125°C**



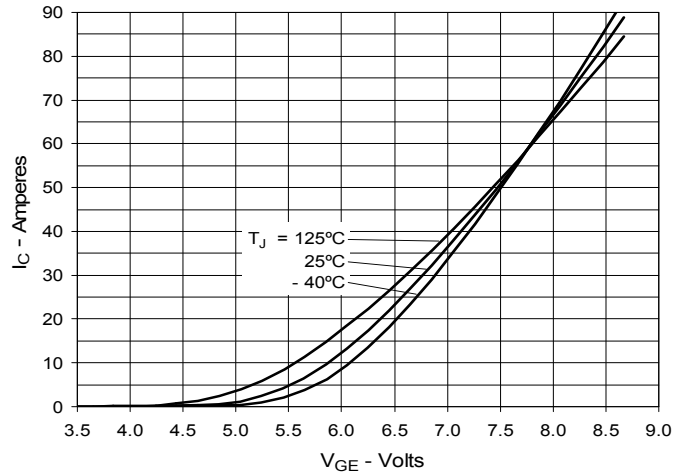
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



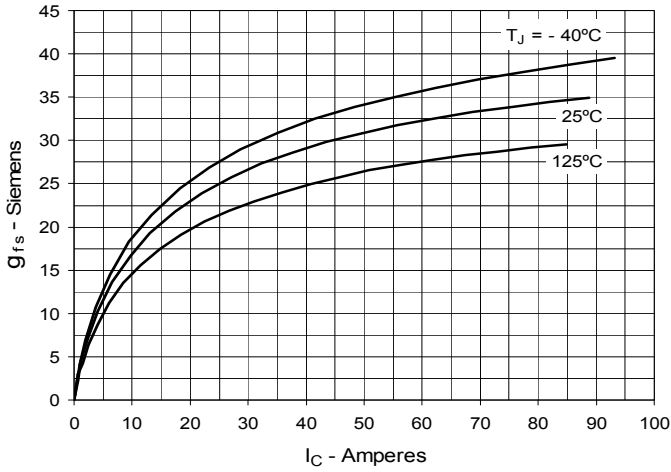
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



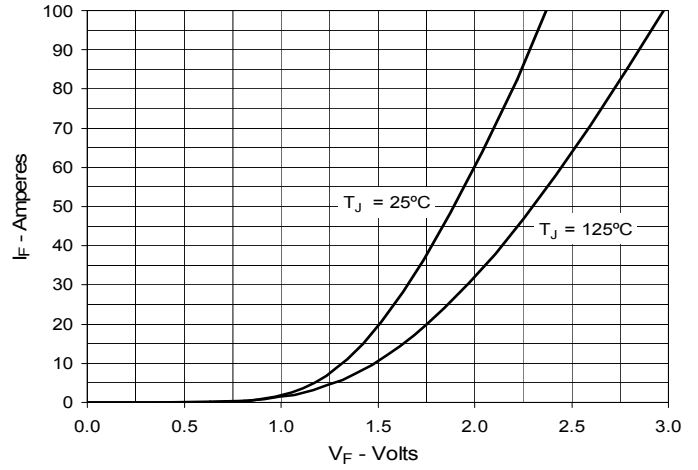
**Fig. 6. Input Admittance**



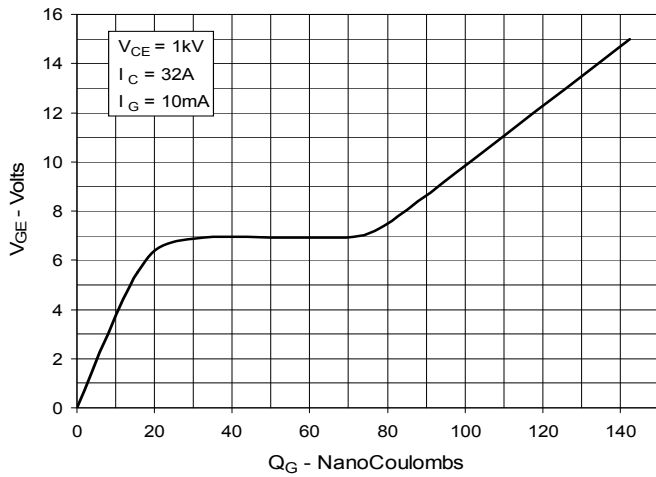
**Fig. 7. Transconductance**



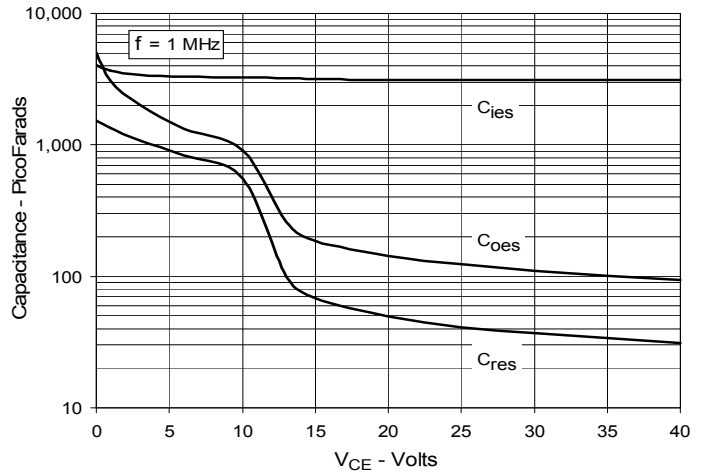
**Fig. 8. Forward Voltage Drop of Intrinsic Diode**



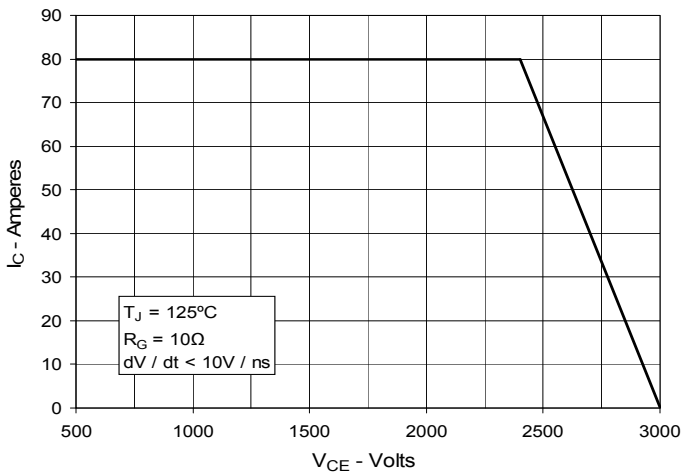
**Fig. 9. Gate Charge**



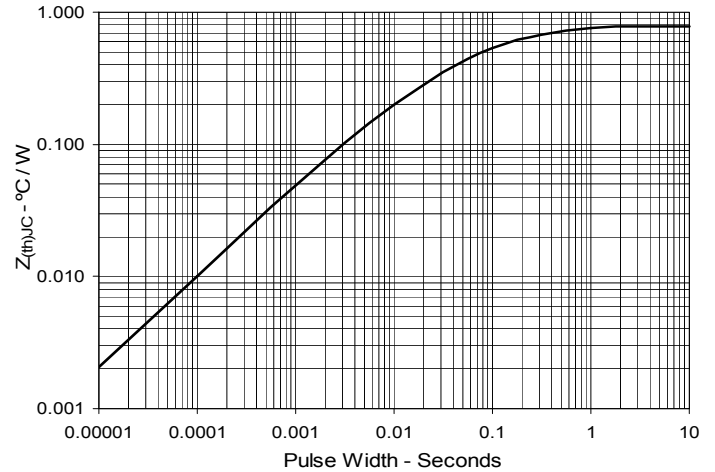
**Fig. 10. Capacitance**



**Fig. 11. Reverse-Bias Safe Operating Area**

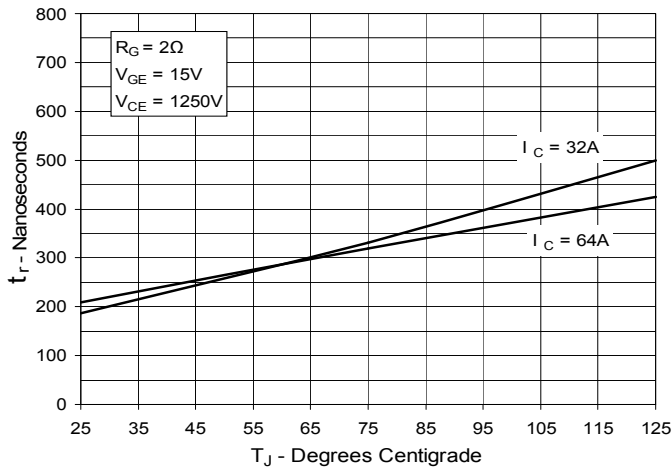


**Fig. 12. Maximum Transient Thermal Impedance**

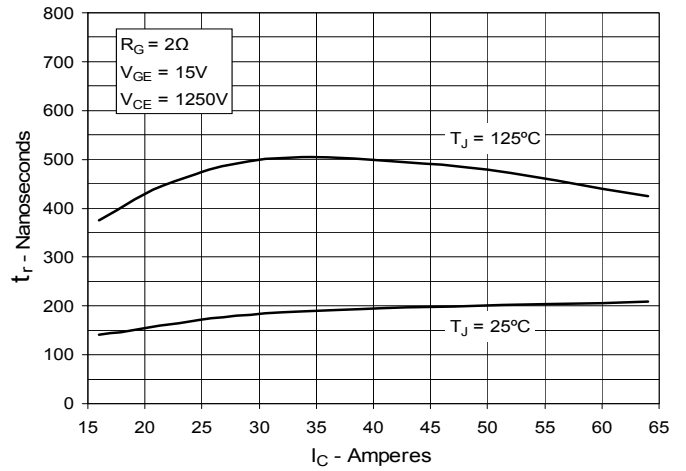


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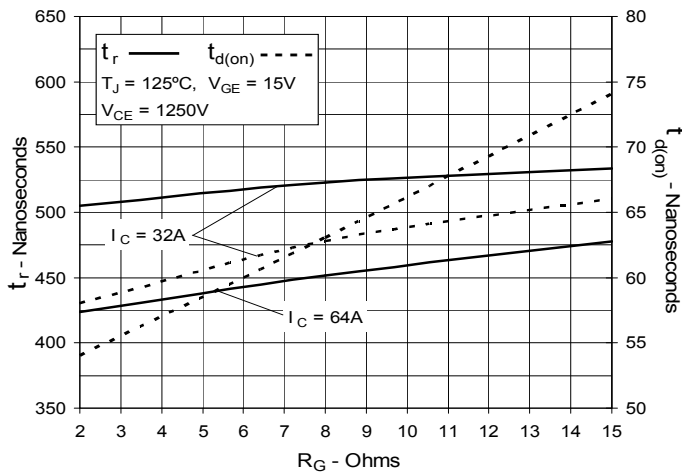
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



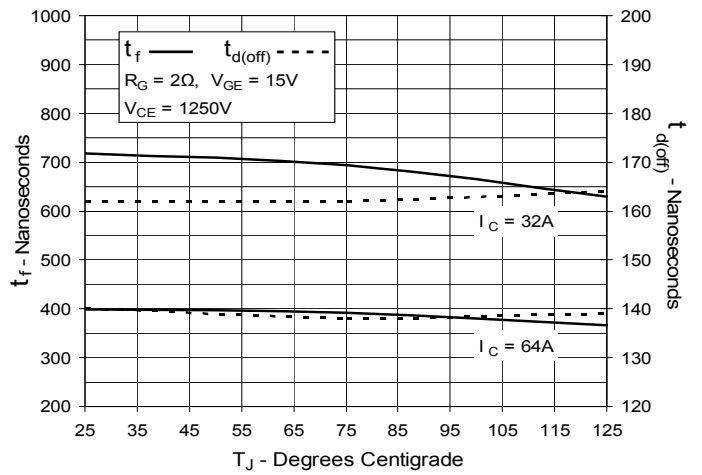
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



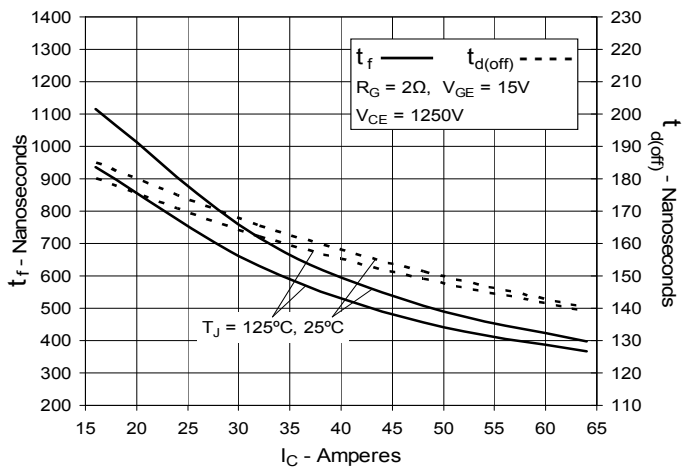
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

